

Silicon NPN Power Transistors

2SC1667

DESCRIPTION

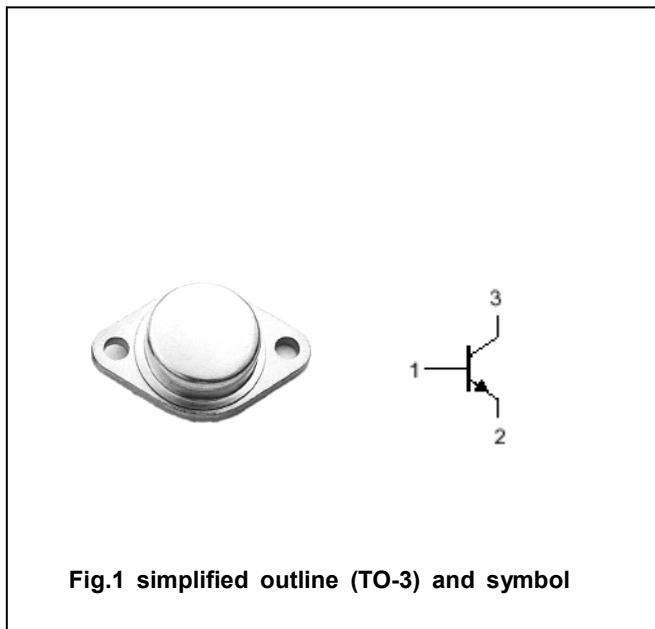
- With TO-3 package
- Low collector saturation voltage
- Excellent safe operating area

APPLICATIONS

- For use in high power audio amplifier applications and high voltage switching regulator circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	90	V
V _{CEO}	Collector-emitter voltage	Open base	90	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		4	A
P _D	Total Power Dissipation	T _C =75□	50	W
T _j	Junction temperature		175	□
T _{stg}	Storage temperature		-55~175	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =50mA ; I _B =0	90			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A ; I _B =0.3A			1.0	V
V _{BE sat}	Base-emitter saturation voltage	I _C =3A ; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =90V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V ; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =4V	40		200	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		10		MHz

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PACKAGE OUTLINE

